

ElectroStatic Discharged Protection Devices (ESD) Data Sheet

Description

The UBD8C18L01 includes back-to-back TVS diodes fabricated in a proprietary silicon avalanche technology to provide protection for electronic equipment that may experience destructive electrostatic discharge (ESD). It has industry leading capacitance linearity over voltage making it ideal for RF applications. This capacitance linearity combined with the extremely small package and low insertion loss makes this part well suited for use in antenna line applications for wireless handsets and terminals. The back-to-back configuration provides symmetrical ESD protection for data lines when AC signals are present.



Contact : $\pm 8\text{kV}$
Air : $\pm 15\text{kV}$

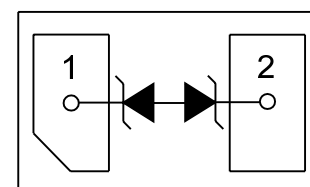


Features

- IEC61000-4-2 ESD 15KV Air, 8KV contact compliance
- SOD882 surface mount package
- Working voltage: 18V
- Low leakage current
- Lead Free/RoHS compliant
- Flammability rating UL 94V-0
- Meets MSL level 1, per J-STD-020
- Marking: B18

Applications

- RF Signal ESD Protection
- NFC Antenna Protection
- MP3/ PMP
- Portable Medical
- Set Top Boxes,
- Smart Phones
- External Storage
- Ultrabooks, Notebooks
- Tablets, eReaders



Pin Configuration

Maximum Ratings

Rating	Symbol	Value	Unit
Peak pulse current ($t_p=8/20\mu\text{s}$)	I_{PP}	2	A
ESD voltage (Contact discharge)	V_{ESD}	± 8	kV
ESD voltage (Air discharge)		± 15	
Lead soldering temperature	T_L	260	$^{\circ}\text{C}$
Storage & operating temperature range	T_{STG}, T_J	-50~+150	$^{\circ}\text{C}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				18	V
Reverse breakdown voltage	V_{BR}	$I_{BR}=1\text{mA}$	19			V
Reverse leakage current	I_R	$V_R=18\text{V}$			1	μA
Clamping voltage ($t_p=8/20\mu\text{s}$)	V_C	$I_{PP}=1\text{A}$			30	V
Clamping voltage ($t_p=8/20\mu\text{s}$)	V_C	$I_{PP}=2\text{A}$			35	V
Off state junction capacitance	C_J	$0\text{Vdc}, f=1\text{MHz}$		0.4	0.6	pF

Typical Characteristics Curves

Figure 1. Insertion Loss (S21) I/O to GND

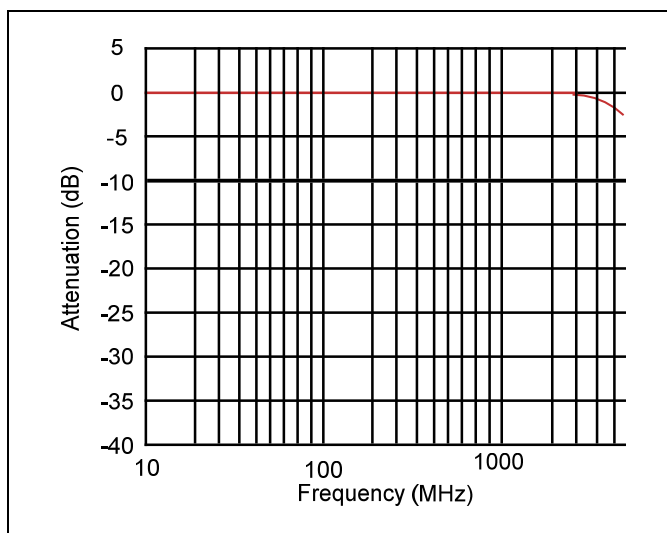


Figure 2. Capacitance vs. Bias Voltage

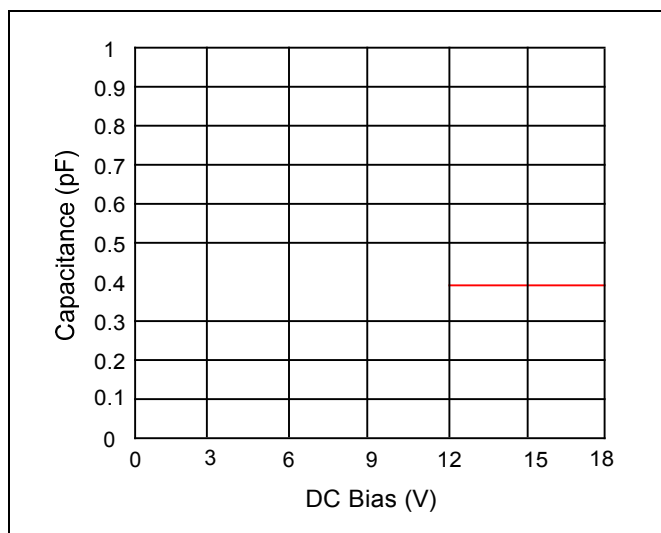


Figure 3. Pulse Waveform

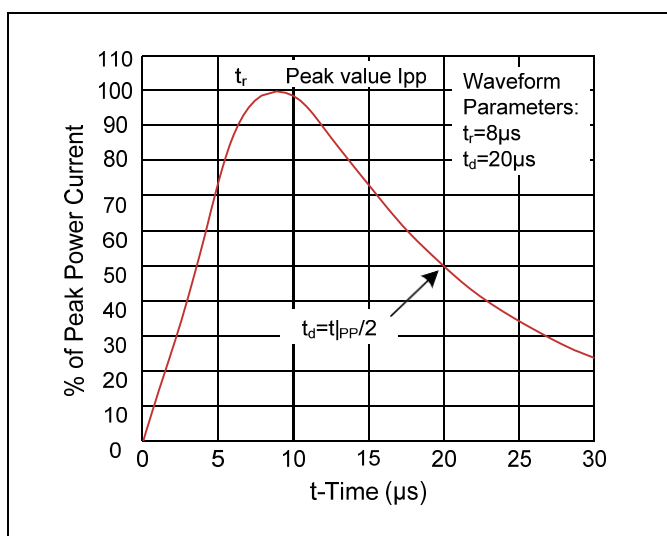
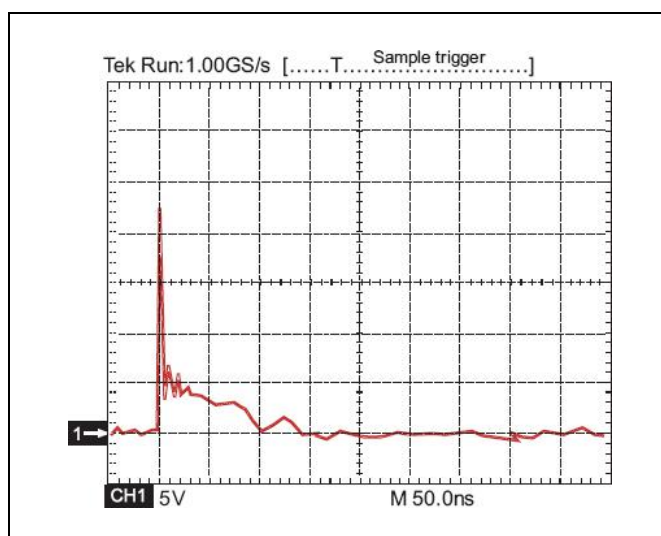
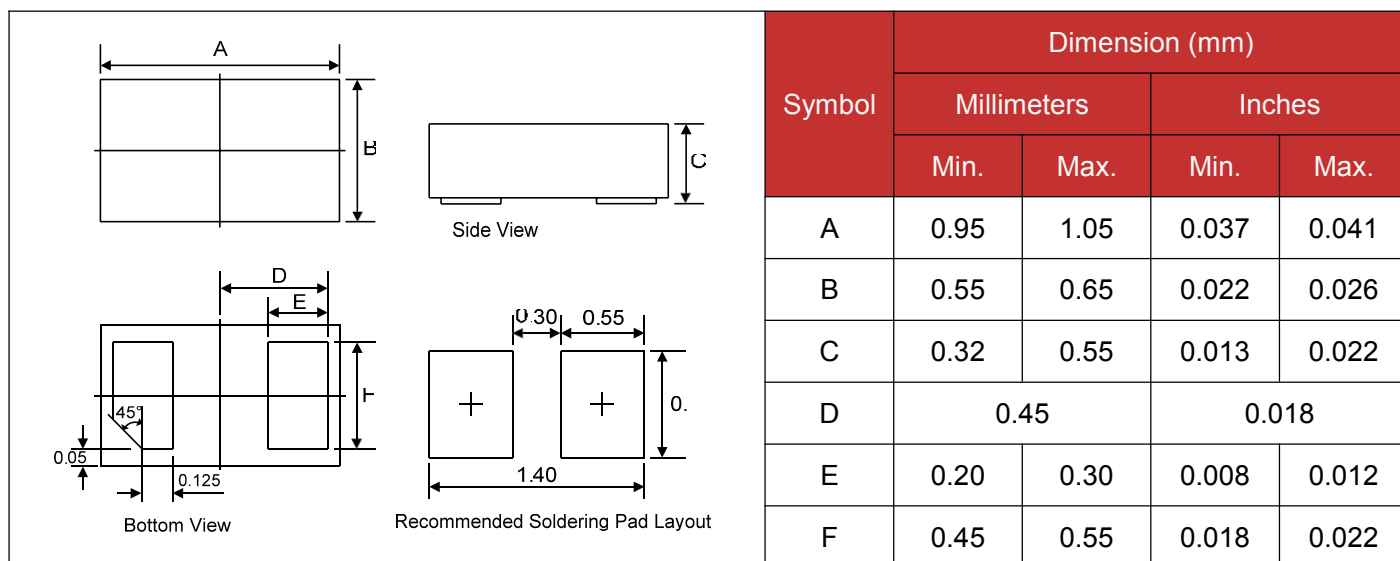


Figure 4. ESD Clamping (8kV Contact IEC61000-4-2)



Dimensions (SOD882)



Packaging

